


The attached Appendix includes marked-up copies of each rewritten claim (37 C.F.R. §1.121(c)(1)(ii)).

Respectfully submitted,


James A. Oliff
Registration No. 27,075

Joel S. Armstrong
Registration No. 36,430

JAO:JSA/zmc

Attached: APPENDIX

Date: February 28, 2002

OLIFF & BERRIDGE, PLC
P.O. Box 19928
Alexandria, Virginia 22320
Telephone: (703) 836-6400

<p>DEPOSIT ACCOUNT USE AUTHORIZATION Please grant any extension necessary for entry; Charge any fee due to our Deposit Account No. 15-0461</p>
--

202220-15269001

APPENDIX

Changes to Specification:

Page 1, between lines 1 and 2, new paragraphs are added.

Page 1, between lines 4 and 5, a new paragraph is added.

Page 2, between lines 10 and 11, a new paragraph is added.

Page 4, between lines 16 and 17, a new paragraph is added.

Page 5, between lines 13 and 14, a new paragraph is added.

Changes to Claims:

The following are marked-up versions of the amended claims:

3. (Amended) A method as claimed in claim 1 ~~or claim 2~~ wherein holes (12;39) are etched and filled with metal (13;40) to allow contacts to be made to the filters (2;28).

4. (Amended) A method as claimed in claim 1 ~~or claim 2~~ wherein metal layers (44) are deposited on the edges of the filters (28) after they have been separated in order to allow contacts to be made to the filters.

5. (Amended) A method as claimed in claim 1 ~~any one of the preceding claims~~ wherein a third wafer (14;34) is bonded to the first wafer (1;27) on that face remote from the second wafer (8;30).

6. (Amended) A method as claimed in claim 1 ~~any one of the preceding claims~~ wherein one or more of the wafer bonding processes is undertaken under a vacuum.

7. (Amended) A method as claimed in claim 1 ~~any one of the preceding claims~~ wherein one or more of the wafer bonding processes used is anodic bonding employing a borosilicate bonding layer.

8. (Amended) A method as claimed in claim 1 ~~any one of claims 1 to 6~~ wherein one or more of the wafer bonding processes used employs a low melting point glass as the bonding layer and the bond is made by a combination of heat and pressure.

9. (Amended) A method as claimed in claim 1 ~~any one of claims 1 to 6~~ wherein one or more of the wafer bonding processes used employs a metal or alloy as the bonding layer and the bond is made by a combination of heat and pressure.

10. (Amended) A filter made by the method according to claim 1 ~~any one of the preceding claims~~.

208220 45269001